N4MNC011

30V Dual N-Channel MOSFETs

BV_{DSS}	$R_{DS(ON)}$	I_D
30 V	11 mΩ	9 A

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

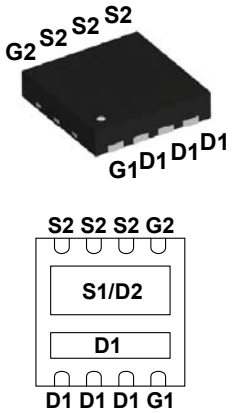
Features

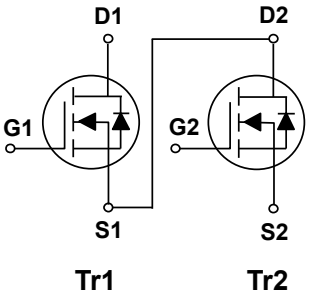
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

DFN3X3A Pin Configuration





Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous (T_C=25°C)	9	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	36	A
IAS	Single Pulse Avalanche Current (NOTE 2)	16	A
P_D	Power Dissipation (T_C=25°C)	1.47	W
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		NC011 , DB3810H	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	85	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25°C	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=6A	---	---	11	mΩ
		V_{GS}=4.5V , I_D=3A	---	---	15	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250uA	1.2	---	2.5	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=8A	---	5.6	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=10V , I_D=1A	---	23.2	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	3.7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=10V , V_{GS}=10V , R_{GEN}=2.7 Ω , I_D=1A (NOTE 2)	---	5.4	---	nS
T_r	Rise Time		---	43	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.5	---	
T_f	Fall Time		---	29.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , F=1MHz	---	900	---	pF
C_{oss}	Output Capacitance		---	131	---	
C_{rss}	Reverse Transfer Capacitance		---	96	---	
R_g	Gate Resistance	V_{GS}=0V , V_{DS}=0V , F=1MHz	---	3.2	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	9	A
I_{SM}	Pulsed Source Current		---	---	18	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1	V

NOTES：

1.Repetitive Rating：Pulsed width limited by maximum junction temperature.

2.V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=16A, R_G=25Ω, Starting T_J=25°C.

3.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.

4.Essentially independent of operating temperature.

5.It is the same characteristics for Tr1 and Tr2.

Characteristics Curves

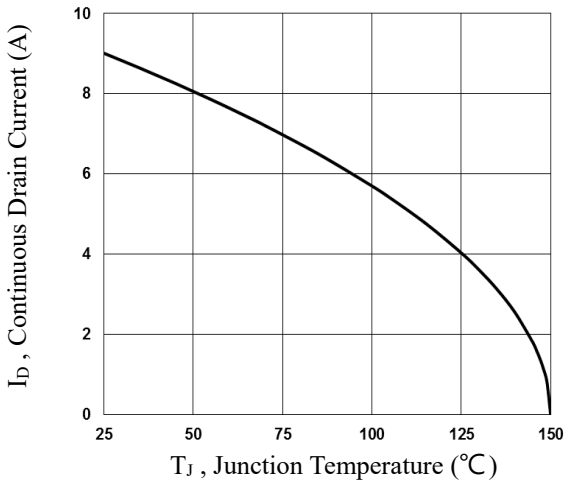


Fig.1 Continuous Drain Current vs. T_C

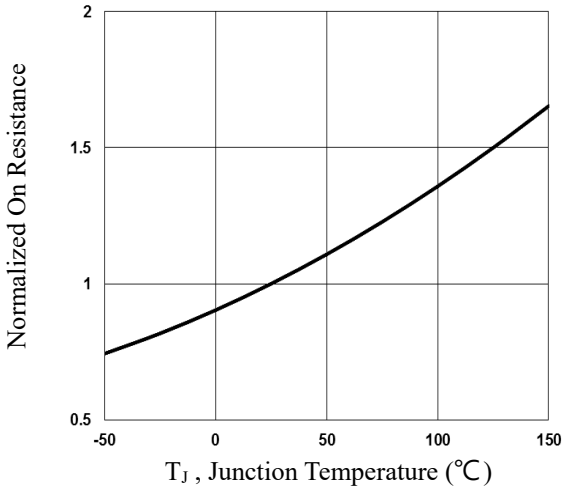


Fig.2 Normalized RDSON vs. T_J

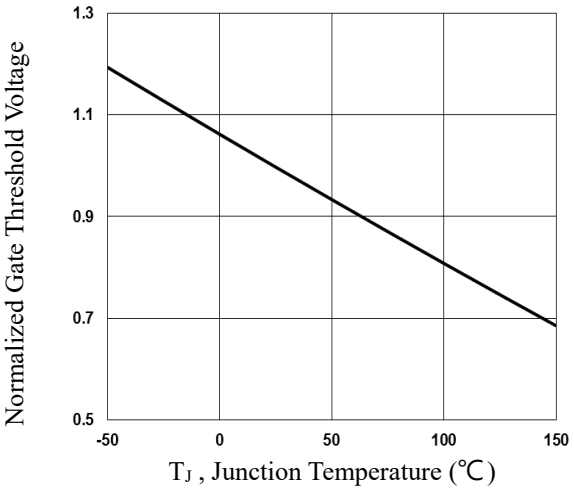


Fig.3 Normalized V_{th} vs. T_J

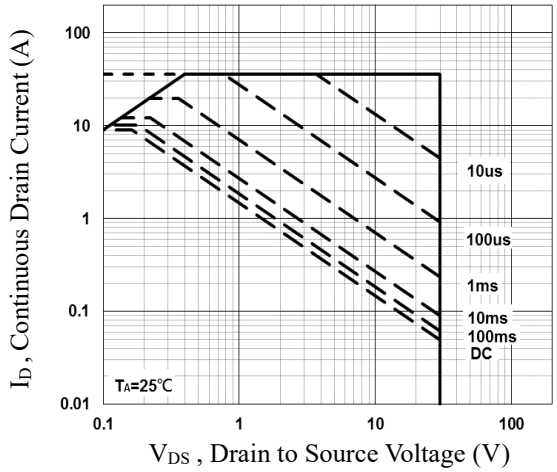


Fig.4 Maximum Safe Operation Area

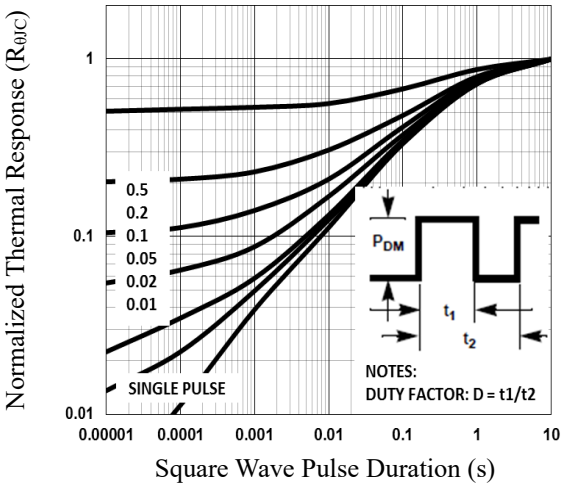


Fig.5 Normalized Transient Impedance

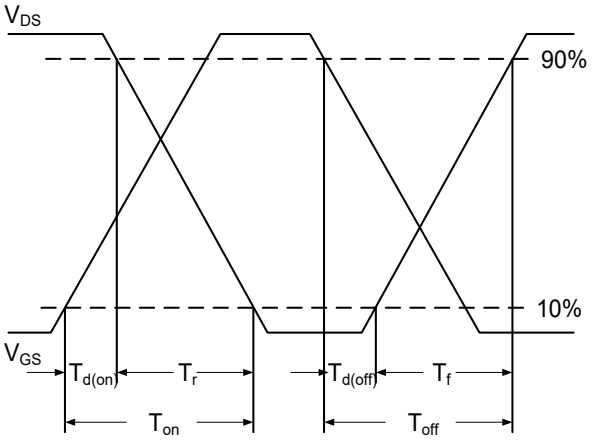
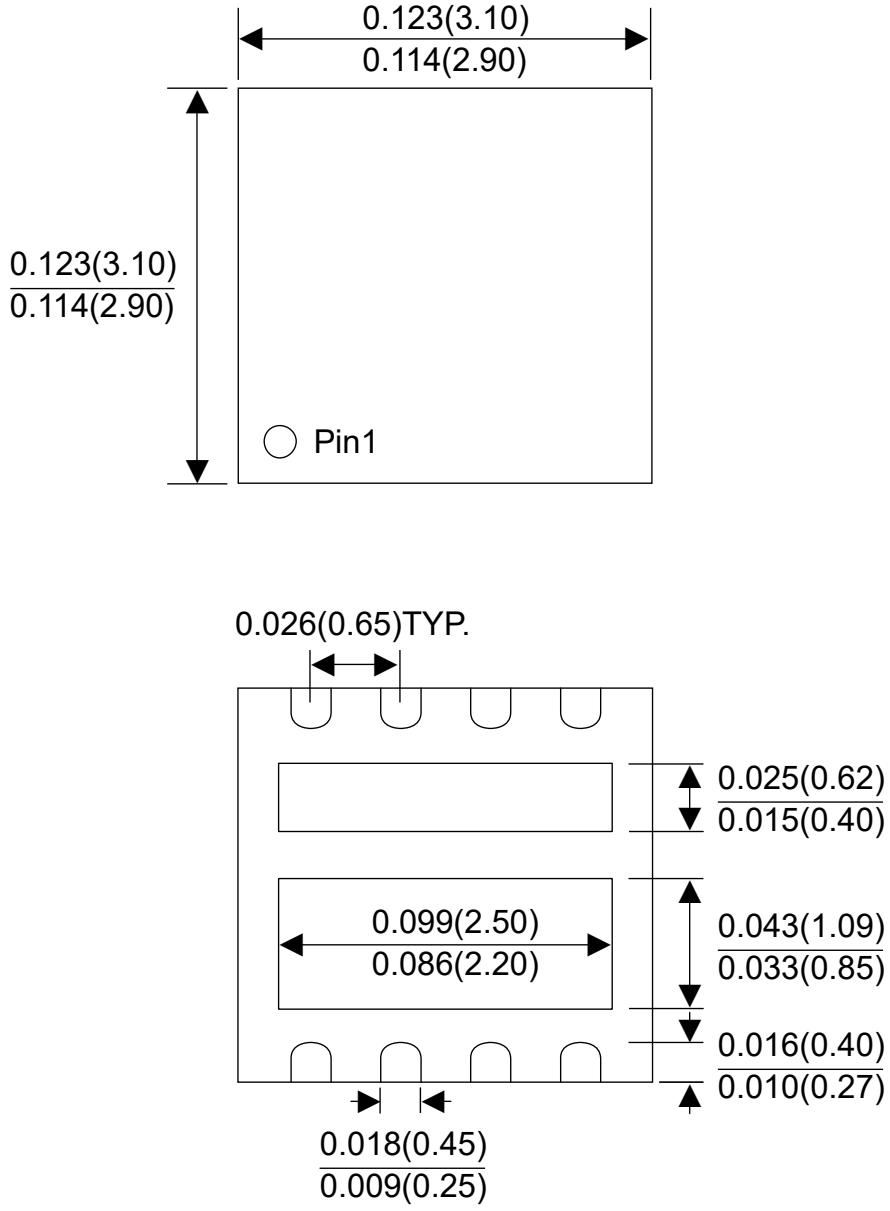


Fig.6 Switching Time Waveform

Package Outline Dimensions



DFN3X3A

Dimensions in inches and (millimeters)

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